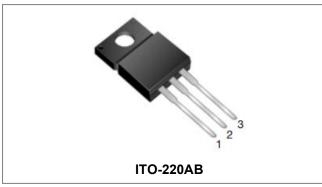




# MBRF30120CT SCHOTTKY RECTIFIER



### **Features**

- 175°C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- **Reverse battery protection**

# Maximum Ratings@Tc=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ \end{array}$	-	120	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=111°C, In DC	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	200	А

### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.85	0.90	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.001	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	1.3	15.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	311	400	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T <sub>A</sub> = 25 °C)	V <sub>ISO</sub>	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
,		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •

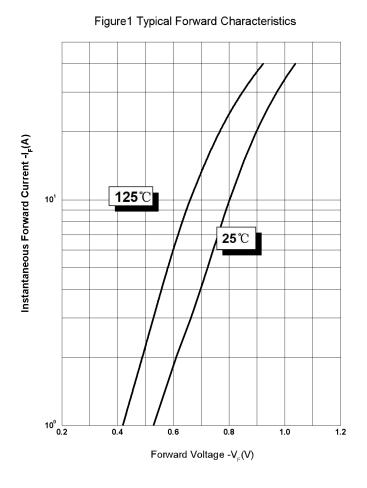


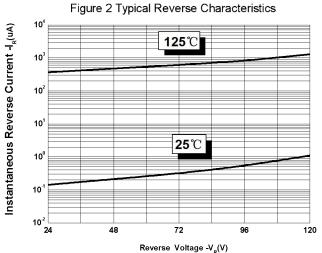


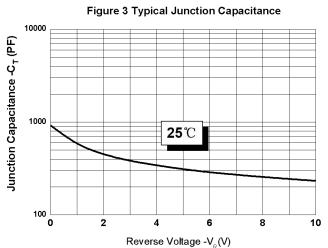
# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	4.5	°C/W
Approximate Weight	wt	-	2	g
Case Style	ITO-220AB			

# **Ratings and Characteristics Curves**







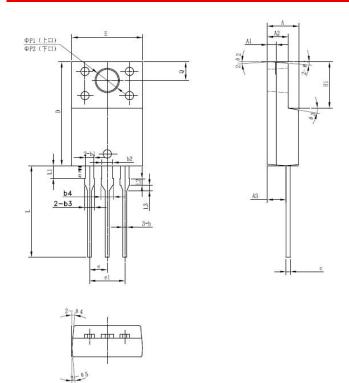
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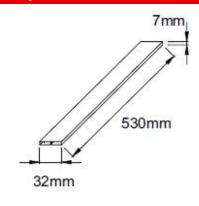


# **Mechanical Dimensions ITO-220AB**



SYMBOL	Millimeters				
STWIBUL	MIN.	TYP.	MAX.		
Α	4.30	4.50	4.70		
A1	1.10	1.30	1.50		
A2	2.80	3.00	3.20		
A3	2.50	2.70	2.90		
b	0.50	0.60	0.75		
b1	1.10	1.20	1.35		
b2	1.50	1.60	1.75		
b3	1.20	1.30	1.45		
b4	1.60	1.70	1.85		
С	0.50	0.60	0.75		
D	14.80	15.00	15.20		
E	9.96	10.16	10.36		
е		2.55			
e1		5.10			
H1	6.50	6.70	6.90		
L	12.70	13.20	13.70		
L1	1.60	1.80	2.00		
L2	0.80	1.00	1.20		
L3	0.60	0.80	1.00		
ФР1( 上□)	3.30	3.50	3.70		
<b>ΦP2</b> (下口)	2.99	3.19	3.39		
Q	2.50	2.70	2.90		
Θ1		5°			
Θ2		4°			
Θ3		10°			
Θ4		5°			
Θ5		5°			

# **Tube Specification**



# **Marking Diagram**



### Where XXXXX is YYWWL

 MBR
 = Device Type

 F
 = Package type

 30
 = Forward Current (30A)

 120
 = Reverse Voltage (120V)

 CT
 = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

 Cautions: Molding resin

 Epoxy resin UL:94V-0

# **Ordering Information**

Device	Package	Shipping
MBRF30120CT	ITO-220AB (Pb-Free)	50 pcs/ tube

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •





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